MY4446A
30V N-Channel Enhancement Mode MOSFET

MAOYUANWEI semiconductor

General Description

The MY4446A uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.
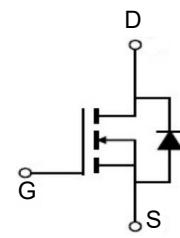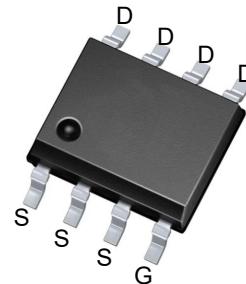
: YUh fYg

X_{FUU}	30	X
K_f	8	C
$T_{FU*QP+*cvXI\ U?10X+}$	19	o á
$T_{FU*QP+*cvXI\ U?4.5X+}$	24	o á

Application

➢ Battery Áprotection
➢ Š[æåÁ¸ ã&@
➢ W¸ã¸c^¦¡ˇ]æã|^Á¸[¸^¦Áˇ]]|^

DUW_U[Y A Uf_]b[UbX CfXYf]b[±bZcfa Uh}cb

DfcXi Wﬁ=8	DUW_	A Uf_]b[	E hﬁfD7 GŁ
MY4446A	ÙUÚË	NULL	H€€€

5 Vgc`i hˇA UI]a i a ˇFUh}b[g˙fH₇1&) ℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	$\pm$20	V
$I_D@T_A=25°C$	Continuous Drain Current, V_{GS} @ 10V[1]	8	A
$I_D@T_A=70°C$	Continuous Drain Current, V_{GS} @ 10V[1]	5.8	A
I_{DM}	Pulsed Drain Current[2]	30	A
EAS	Single Pulse Avalanche Energy[3]	20	mJ
I_{AS}	Avalanche Current	22	A
$P_D@T_A=25°C$	Total Power Dissipation[4]	4.5	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	50	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	30	°C/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	33	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.027	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=10A	---	19	28	mΩ
		V_{GS}=4.5V , I_D=8A	---	24	40	
$V_{GS(th)}$	Gate Threshold Voltage		1.0	1.5	2.4	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient	V_{GS}=V_{DS} , I_D =250uA	---	-5.8	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=24V , V_{GS}=0V , T_J=55℃	---		10	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=10A	---	5.8	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2.2	3.8	
Q_g	Total Gate Charge (4.5V)		---	12.6	17.6	nC
Q_{gs}	Gate-Source Charge	V_{DS}=15V , V_{GS}=4.5V , I_D=10A	---	4.2	5.9	
Q_{gd}	Gate-Drain Charge		---	5.1	7.1	
$T_{d(on)}$	Turn-On Delay Time		---	6.2	12.4	ns
T_r	Rise Time	V_{DD}=15V , V_{GS}=10V , R_G=3.3 I_D=10A	---	59	106	
$T_{d(off)}$	Turn-Off Delay Time		---	27.6	55	
T_f	Fall Time		---	8.4	16.8	
C_{iss}	Input Capacitance		---	960	---	pF
C_{oss}	Output Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	139	---	
C_{rss}	Reverse Transfer Capacitance		---	87	---	
I_s	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	10.3	A
I_{SM}	Pulsed Source Current[2,5]		---	---	42	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_s=1A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	IF=10A, dI/dt=100A/μs, T_J=25℃	---	12.5	---	nS
Q_{rr}	Reverse Recovery Charge		---	5	---	nC

Note :

1 .The data tested by surface mounted on a 1 inch[2] FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3 .The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=35A

4.The power dissipation is limited by 150℃ junction temperature 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics
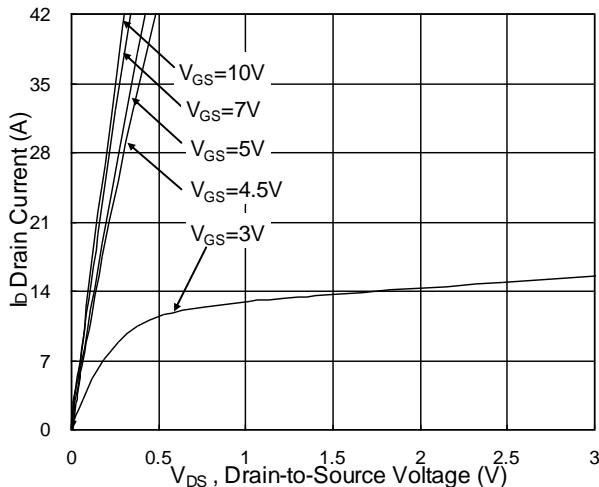

Fig.1 Typical Output Characteristics
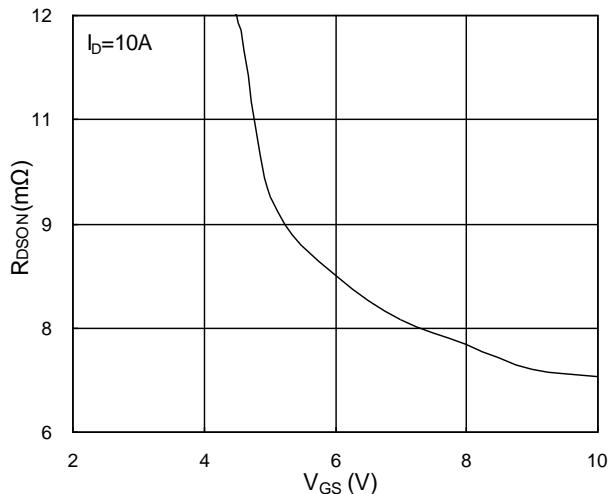

Fig.2 On-Resistance vs. Gate-Source
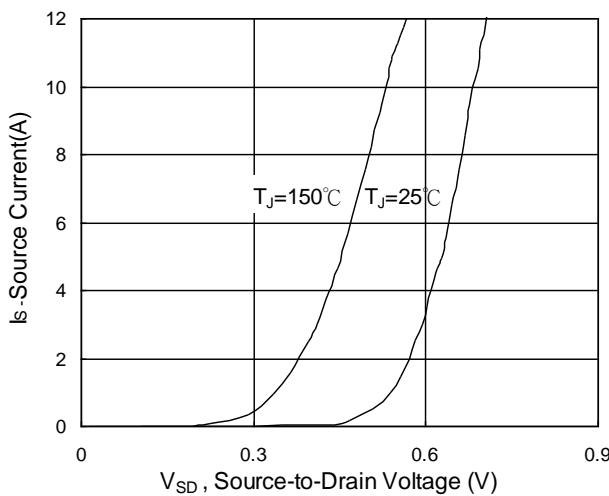


Fig.3 Forward Characteristics of reverse
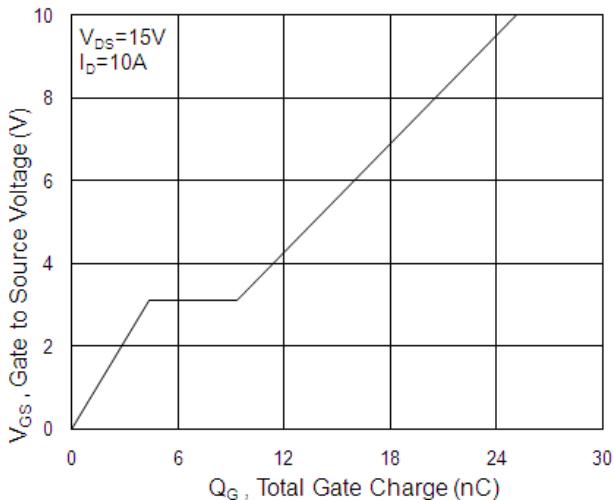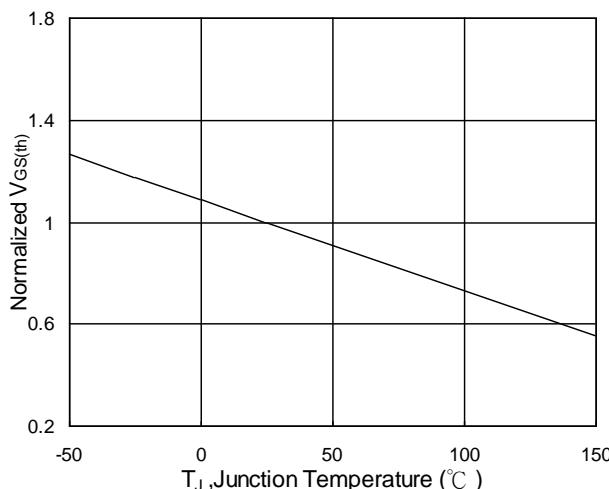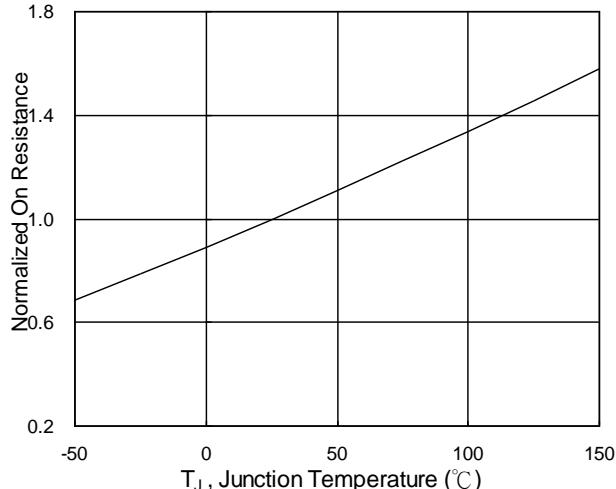
Fig.4 Gate-Charge Characteristics


Fig.5 Normalized V$_{GS(th)}$ vs. T$_J$

**Fig.6 Normalized R$_{DSON}$ vs. T$_J$**
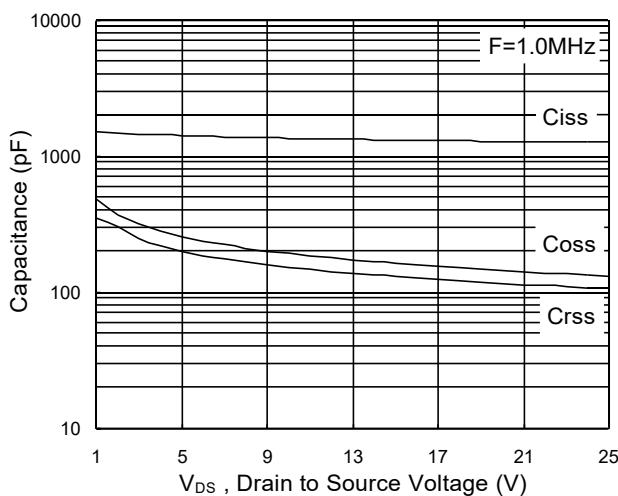
Fig.7 Capacitance
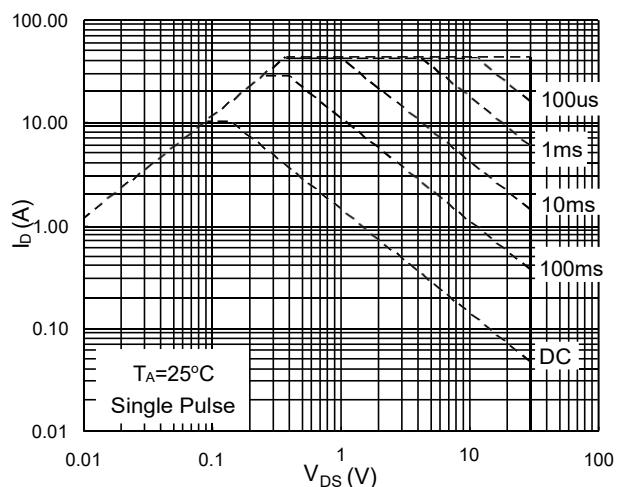
**Fig.8 Safe Operating Area**
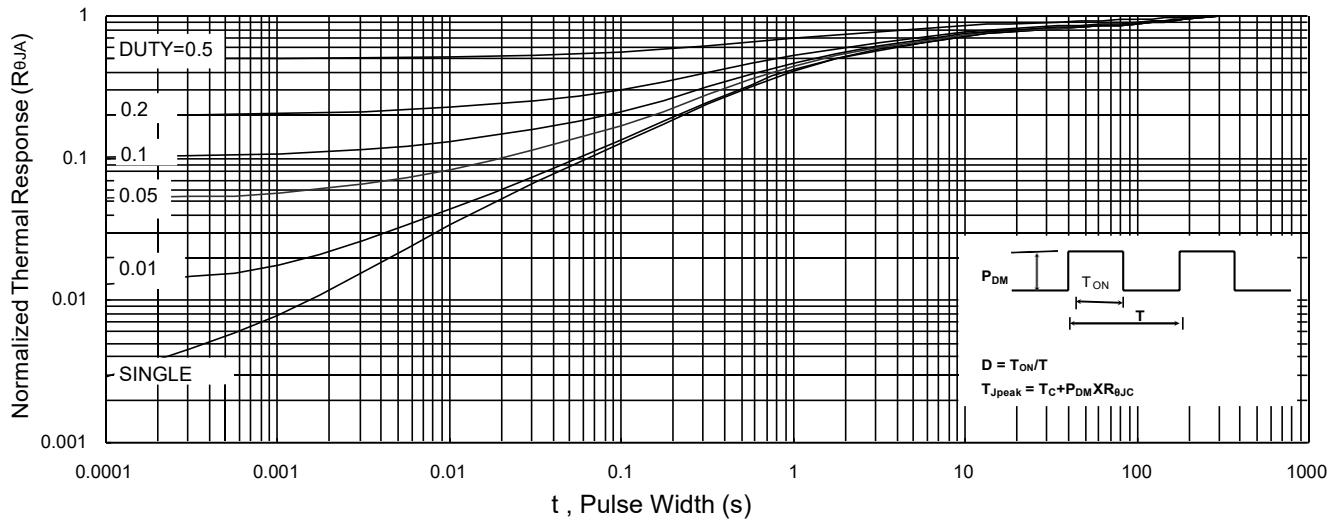
Fig.9 Normalized Maximum Transient Thermal Impedance
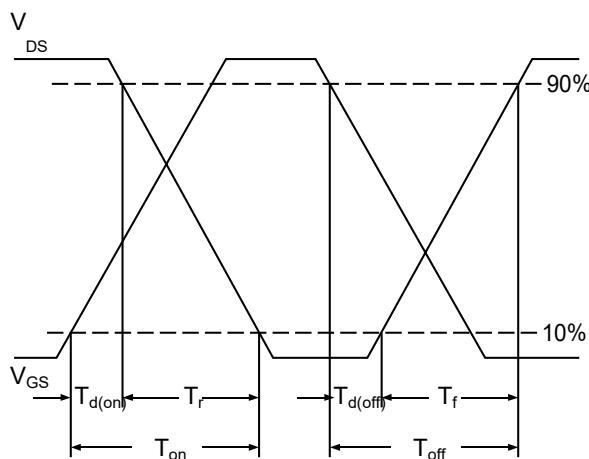
Fig.10 Switching Time Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS}-V_{DD}}$$
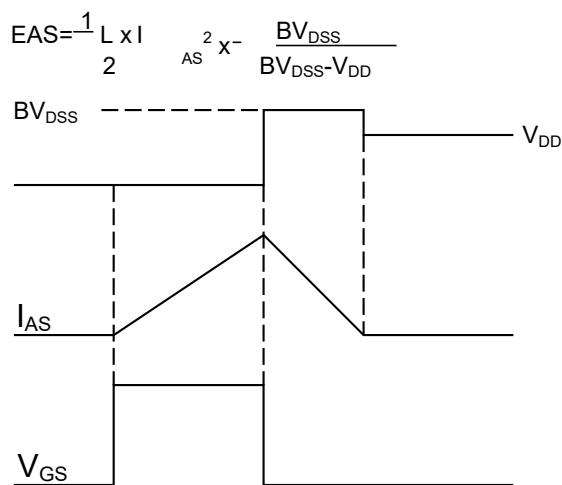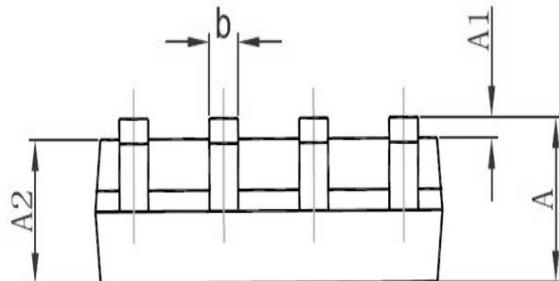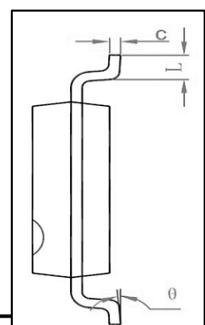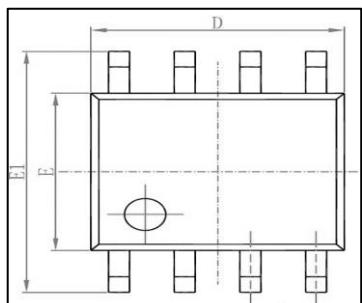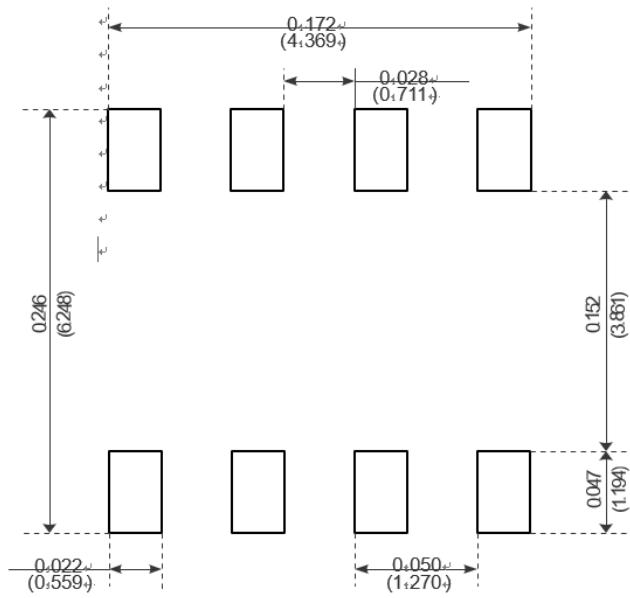
Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data-SOP-8

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Recommended Minimum Pads